

SUBSTRATE PROCESSING METHOD, METHOD FOR MANUFACTURING
SEMICONDUCTOR DEVICE, PROGRAM, AND SUBSTRATE PROCESSING DEVICE

ABSTRACT

Provided is a technique with which it is possible to control the orientation of crystal particles in a film (or in a layer). The method includes a step for forming a film on a substrate by performing a cycle for forming layers on the substrate a prescribed number of times by performing (a) a step for supplying a raw material gas containing a halogen element to the substrate, and (b) a step for supplying a reaction gas to the substrate, the cycles being performed under a prescribed formation condition on the basis of a prescribed relationship between the amount of the halogen element included in the layer and the proportion of the film occupied by crystal particles oriented in a prescribed crystal plane.

Fig. 3